

# FDMB3800N

## Dual N-Channel PowerTrench® MOSFET

30V, 4.8A, 40mΩ

### Features

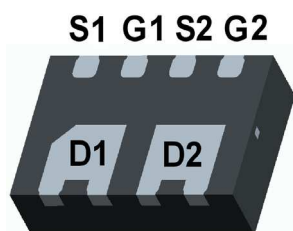
- Max  $r_{DS(on)}$  = 40mΩ at  $V_{GS}$  = 10V,  $I_D$  = 4.8A
- Max  $r_{DS(on)}$  = 51mΩ at  $V_{GS}$  = 4.5V,  $I_D$  = 4.3A
- Fast switching speed
- Low gate Charge
- High performance trench technology for extremely low  $r_{DS(on)}$
- High power and current handling capability.
- RoHS Compliant



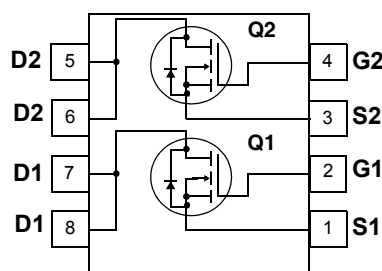
### General Description

These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.



MicroFET 3X1.9



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	4.8	A
	-Pulsed	9	
$P_D$	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	1.6	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1b)	0.75	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	80	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	165	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
3800	FDMB3800N	MicroFET3X1.9	7"	8mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		24		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}$ , $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1 10	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-4		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 4.8\text{A}$		32	40	m $\Omega$
		$V_{GS} = 4.5\text{V}$ , $I_D = 4.3\text{A}$		41	51	
		$V_{GS} = 10\text{V}$ , $I_D = 4.8\text{A}$ , $T_J = 125^\circ\text{C}$		43	61	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{V}$ , $I_D = 4.8\text{A}$		14		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$		350	465	pF
$C_{oss}$	Output Capacitance			90	120	pF
$C_{rss}$	Reverse Transfer Capacitance			40	60	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		3		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{V}$ , $I_D = 1\text{A}$ $V_{GS} = 10\text{V}$ , $R_{GEN} = 6\Omega$		8	16	ns
$t_r$	Rise Time			5	10	ns
$t_{d(off)}$	Turn-Off Delay Time			21	34	ns
$t_f$	Fall Time			2	10	ns
$Q_{g(TOT)}$	Total Gate Charge at 5V	$V_{GS} = 0\text{V}$ to $5\text{V}$ $V_{DD} = 15\text{V}$		4	5.6	nC
$Q_{gs}$	Gate to Source Gate Charge	$I_D = 7.5\text{A}$		1.0		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			1.5		nC

**Drain-Source Diode Characteristics**

$I_S$	Maximum Continuous Drain - Source Diode Forward Current				1.25	A
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = 1.25\text{A}$ (Note 2)		0.8	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 4.8\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$		17		ns
$Q_{rr}$	Reverse Recovery Charge			7		nC

**Notes:**

1:  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $80^\circ\text{C}/\text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b.  $165^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty cycle < 2.0%.

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

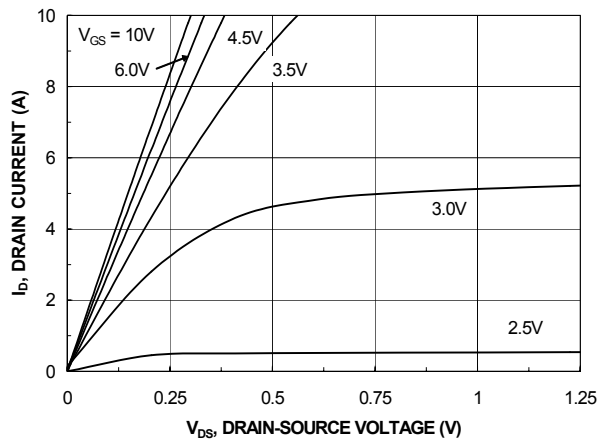


Figure 1. On Region Characteristics

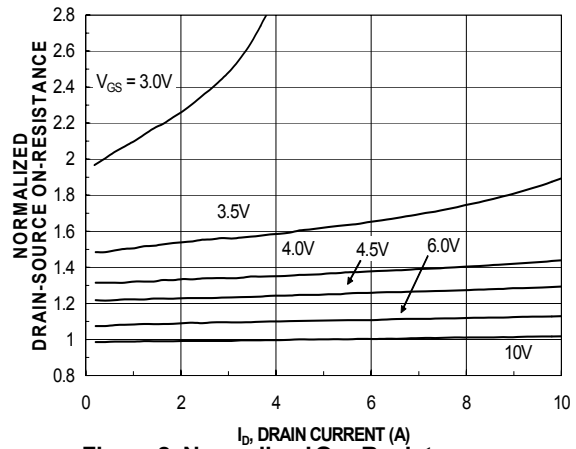


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

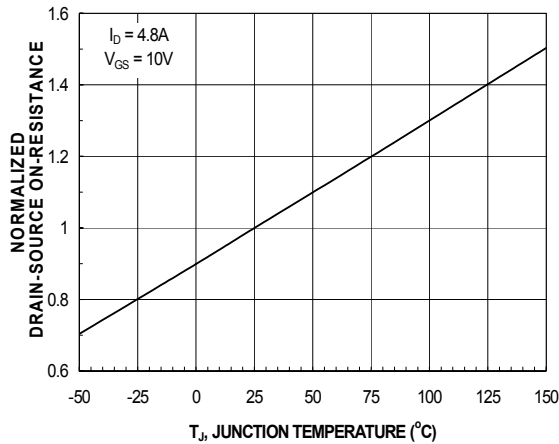


Figure 3. Normalized On-Resistance vs Junction Temperature

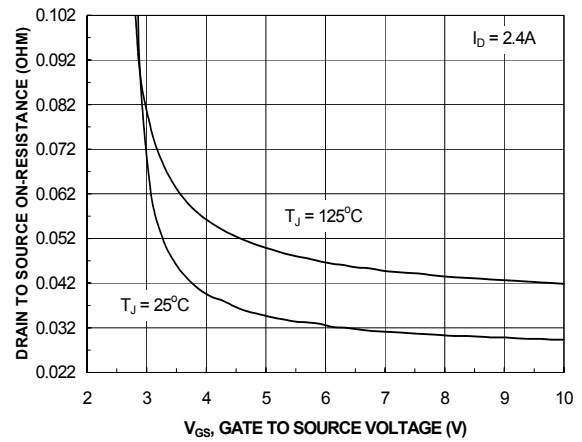


Figure 4. On-Resistance vs Gate to Source Voltage

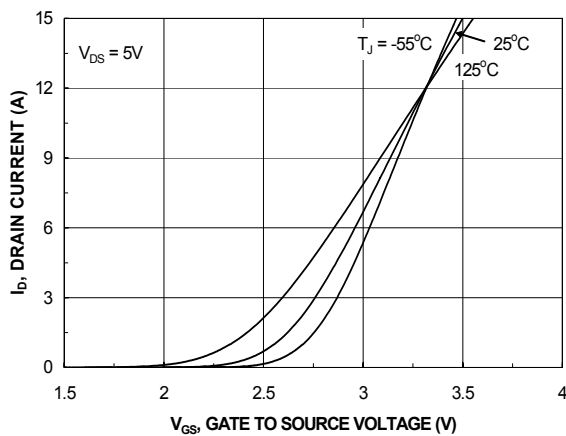


Figure 5. Transfer Characteristics

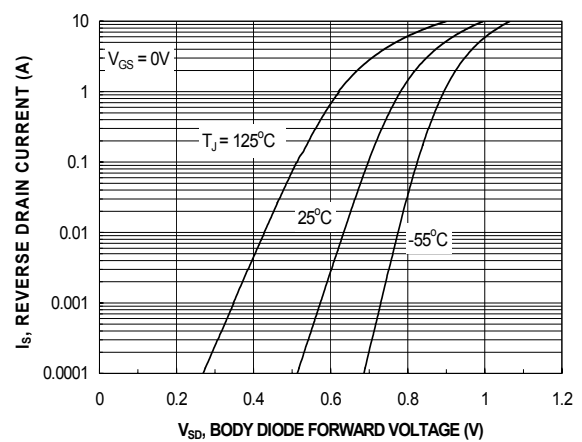


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

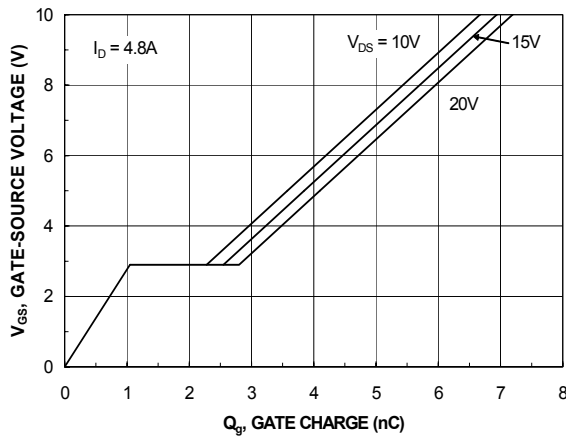


Figure 7. Gate Charge Characteristics

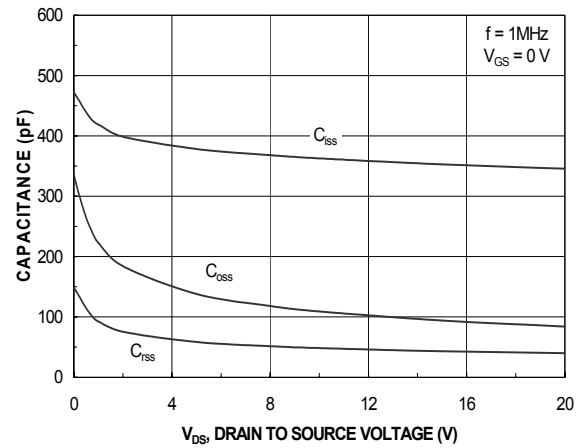


Figure 8. Capacitance vs Drain to Source Voltage

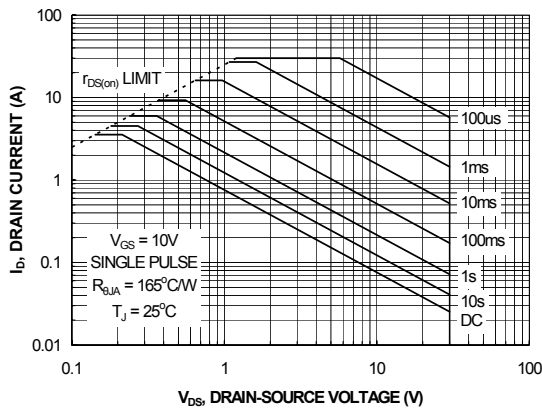


Figure 9. Forward Bias Safe Operating Area

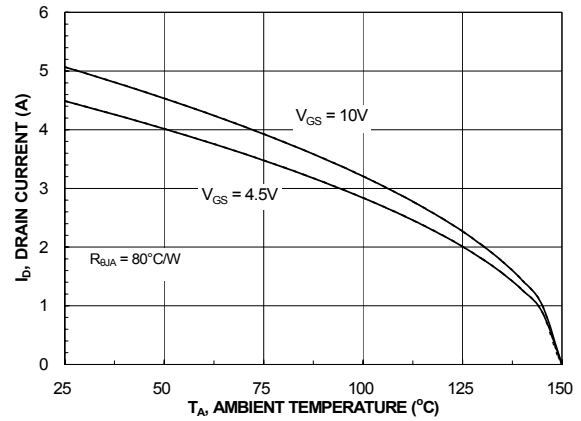


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

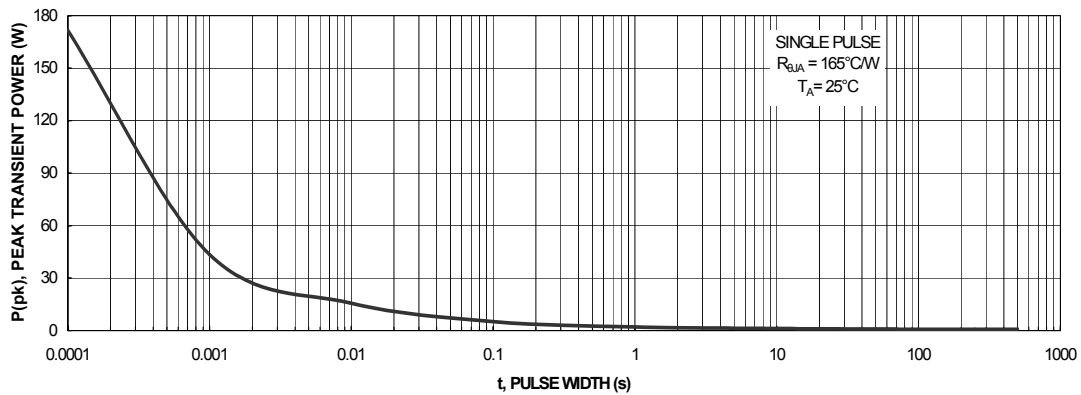
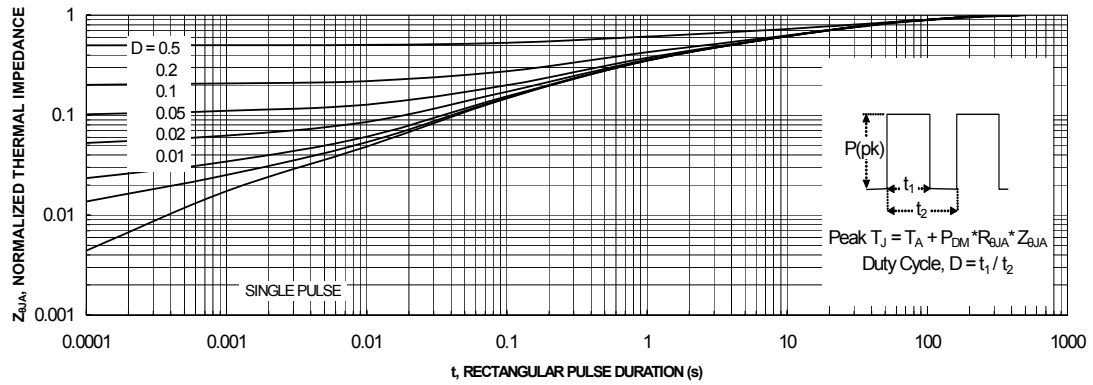


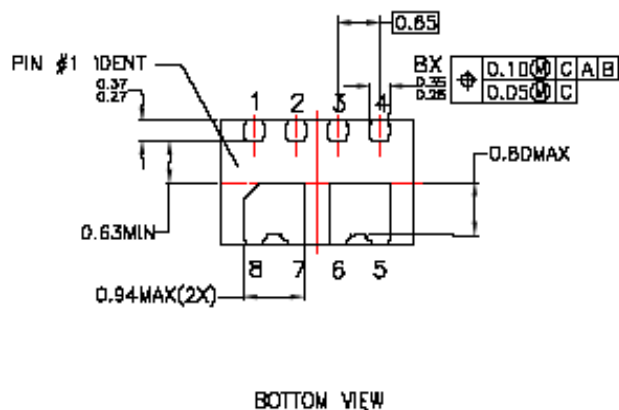
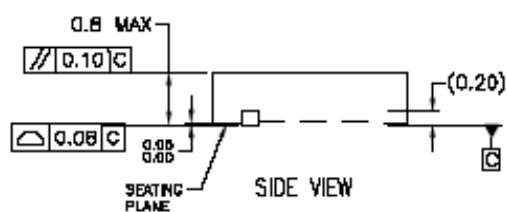
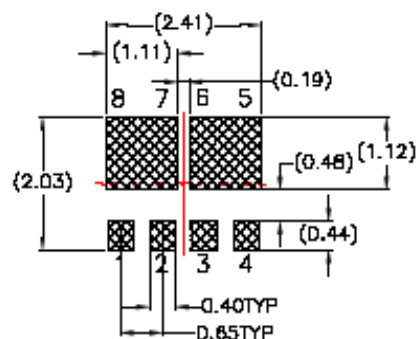
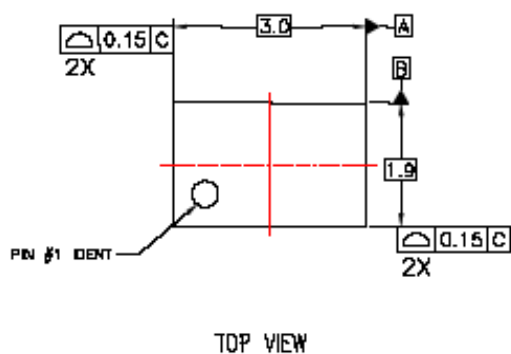
Figure 11. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



**Figure 12. Transient Thermal Response Curve**

# Dimensional Outline and Pad Layout



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